



# **ISC Silicon NPN Power Transistor**

#### **DESCRIPTION**

- · High Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 400(Min)
- Excellent Switching Times-
  - : tr= 1.0  $\mu$  s(Max), tf= 1.0  $\mu$  s(Max)@ I<sub>C</sub>= 4A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

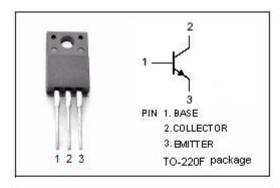
### **APPLICATIONS**

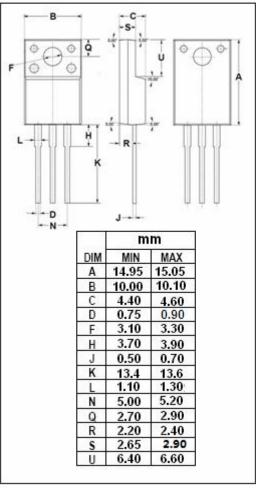


- · Switching regulator application
- High voltage switching application
- High Speed DC-DC converter application
- · Fluorescent light ballastor application

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	500	V	
$V_{\sf CEO}$	Collector-Emitter Voltage	400	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	5	Α	
I <sub>CM</sub>	Collector Current-Peak	7	Α	
l <sub>Β</sub>	Base Current-Continuous	1	Α	
P <sub>C</sub>	Collector Power Dissipation @T <sub>a</sub> =25℃	2	W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	30		
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range -55~150		$^{\circ}$	







## **ISC Silicon NPN Power Transistor**

2SC4371

#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	400			V		
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA ; I <sub>E</sub> = 0	500			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.0	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.5	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 400V; I <sub>E</sub> = 0			100	μ <b>A</b>		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			1	mA		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 3A ; V <sub>CE</sub> = 5V	12					
h <sub>FE-2</sub>	DC Gurrent Gain	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 5V	8					
Switching times								
tr	Rise Time				1.0	μS		
t <sub>stg</sub>	Storage Time	I <sub>B1</sub> = -I <sub>B2</sub> = 0.4A; V <sub>CC</sub> ≈200V R <sub>L</sub> = 50 Ω;P <sub>W</sub> =20 μ s Duty≤1%			2.5	μS		
tf	Fall Time				1.0	μS		

#### **NOTICE:**

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